

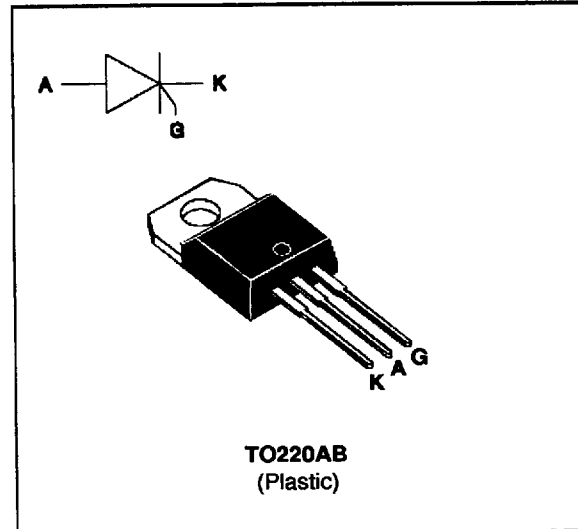
**FEATURES**

- HIGH SURGE CAPABILITY
- HIGH ON-STATE CURRENT
- HIGH STABILITY AND RELIABILITY

**DESCRIPTION**

The TYN 225 ---> TYN 1025 Family Silicon Controlled Rectifiers are high performance glass passivated chips technology.

This general purpose Family Silicon Controlled Rectifiers is designed for power supply up to 400Hz on resistive or inductive load.

**ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter		Value	Unit
$I_T(\text{RMS})$	RMS on-state current (180° conduction angle)	$T_c = 95^\circ\text{C}$	25	A
$I_T(\text{AV})$	Average on-state current (180° conduction angle, single phase circuit)	$T_c = 95^\circ\text{C}$	16	A
$I_{\text{TSM}}$	Non repetitive surge peak on-state current ( $T_j$ initial = $25^\circ\text{C}$ )	$t_p = 8.3 \text{ ms}$	260	A
		$t_p = 10 \text{ ms}$	250	
$I^2t$	$I^2t$ value	$t_p = 10 \text{ ms}$	310	$\text{A}^2\text{s}$
$di/dt$	Critical rate of rise of on-state current Gate supply : $I_G = 100 \text{ mA}$ $di_G/dt = 1 \text{ A}/\mu\text{s}$		100	$\text{A}/\mu\text{s}$
$T_{\text{stg}}$ $T_j$	Storage and operating junction temperature range		- 40 to + 150 - 40 to + 125	$^\circ\text{C}$ $^\circ\text{C}$
$T_l$	Maximum lead temperature for soldering during 10 s at 4.5 mm from case		260	$^\circ\text{C}$

Symbol	Parameter	TYN						Unit
		225	425	625	825	1025	1225	
$V_{\text{DRM}}$ $V_{\text{RRM}}$	Repetitive peak off-state voltage $T_j = 125^\circ\text{C}$	200	400	600	800	1000	1200	V

# THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth (j-a)	Junction to ambient	60	°C/W
Rth (j-c) DC	Junction to case for DC	1.3	°C/W

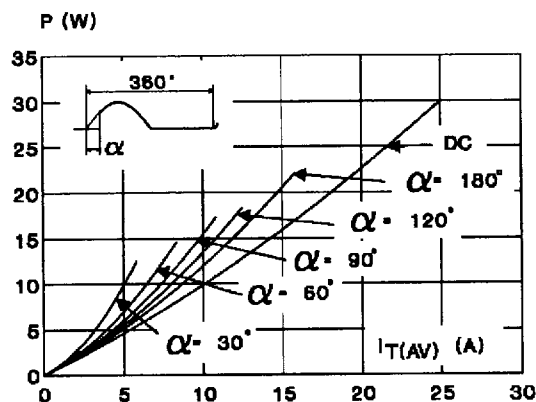
# GATE CHARACTERISTICS (maximum values)

PG (AV) = 1W PGM = 10W (tp = 20 μs) IFGM = 4A (tp = 20 μs) VRGM = 5 V.

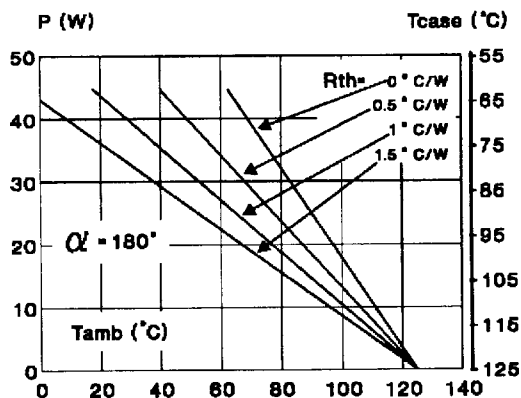
# ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions			Value	Unit
IGT	VD=12V (DC) RL=33Ω	Tj=25°C	MAX	40	mA
VGT	VD=12V (DC) RL=33Ω	Tj=25°C	MAX	1.5	V
VGD	VD=VDRM RL=3.3kΩ	Tj= 125°C	MIN	0.2	V
tgt	VD=VDRM IG = 200mA dIG/dt = 1.5A/μs	Tj=25°C	TYP	2	μs
IL	IG= 1.2 IGT	Tj=25°C	TYP	80	mA
IH	IT= 100mA gate open	Tj=25°C	MAX	50	mA
VTM	ITM= 50A tp= 380μs	Tj=25°C	MAX	1.6	V
IDRM IRRM	VDRM Rated VRRM Rated	Tj=25°C Tj= 125°C	MAX	0.01 4	mA
dV/dt	Linear slope up to VD=67%VDRM gate open	Tj= 125°C	MIN	500	V/μs
tq	VD=67%VDRM ITM= 50A VR= 25V dITM/dt=30 A/μs dVD/dt= 50V/μs	Tj= 125°C	TYP	70	μs

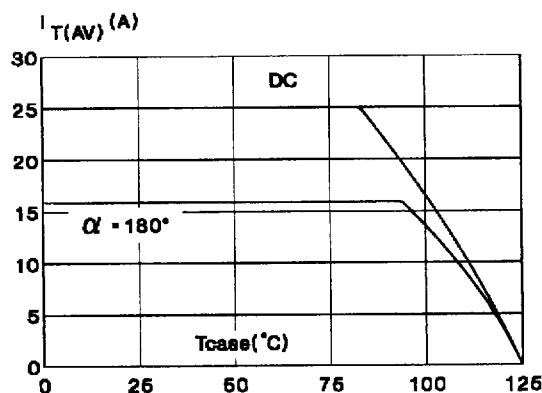
**Fig.1** : Maximum average power dissipation versus average on-state current.



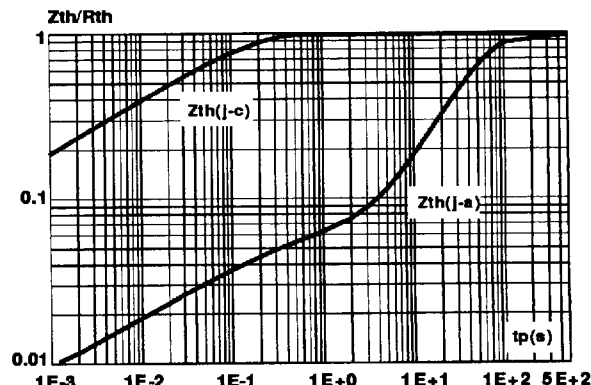
**Fig.2** : Correlation between maximum average power dissipation and maximum allowable temperatures ( $T_{amb}$  and  $T_{case}$ ) for different thermal resistances heatsink + contact.



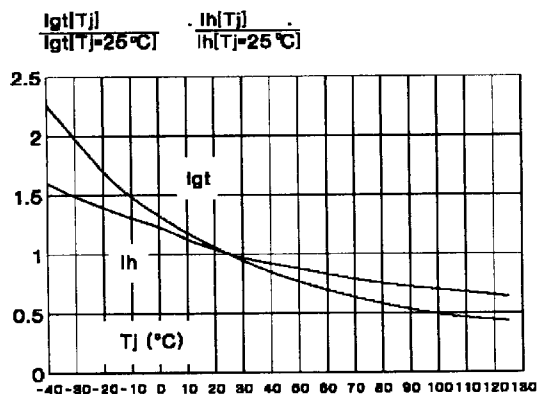
**Fig.3** : Average on-state current versus case temperature.



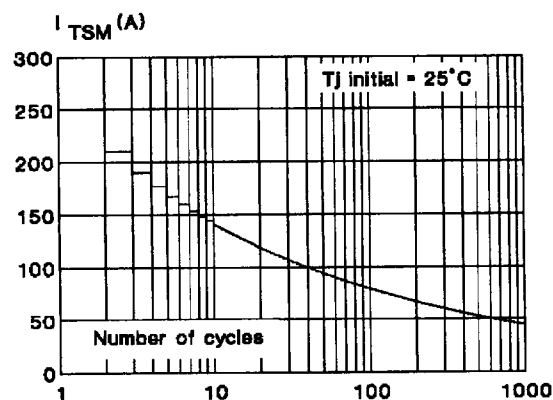
**Fig.4** : Relative variation of thermal impedance versus pulse duration.



**Fig.5** : Relative variation of gate trigger current versus junction temperature.

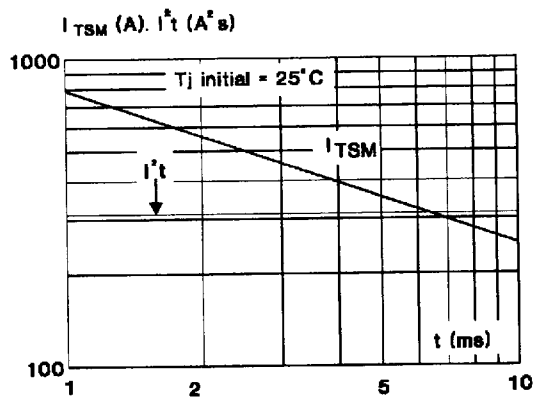


**Fig.6** : Non repetitive surge peak on-state current versus number of cycles.

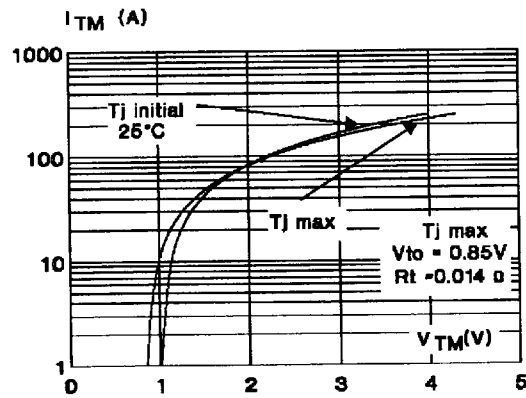


## TYN 225 ---> TYN 1225

**Fig.7 :** Non repetitive surge peak on-state current for a sinusoidal pulse with width :  $t \leq 10$  ms, and corresponding value of  $I^2t$ .

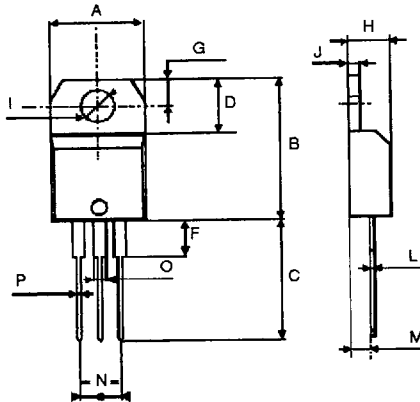


**Fig.8 :** On-state characteristics (maximum values).



## PACKAGE MECHANICAL DATA

### TO220AB Plastic



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	10.00	10.40	0.393	0.409
B	15.20	15.90	0.598	0.625
C	13.00	14.00	0.511	0.551
D	6.20	6.60	0.244	0.259
F	3.50	4.20	0.137	0.165
G	2.65	2.95	0.104	0.116
H	4.40	4.60	0.173	0.181
I	3.75	3.85	0.147	0.151
J	1.23	1.32	0.048	0.051
L	0.49	0.70	0.019	0.027
M	2.40	2.72	0.094	0.107
N	4.80	5.40	0.188	0.212
O	1.14	1.70	0.044	0.066
P	0.61	0.88	0.024	0.034

Cooling method : C  
Marking : type number  
Weight : 2.3 g

Recommended torque value : 0.8 m.N.  
Maximum torque value : 1 m.N.

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